

P-Channel 20 V (D-S) MOSFET

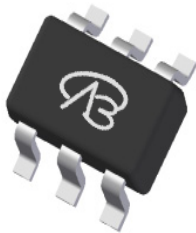
PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 20	0.034 at $V_{GS} = - 4.5$ V	- 4	12.5 nC
	0.045 at $V_{GS} = - 2.5$ V	- 4	
	0.067 at $V_{GS} = - 1.8$ V	- 4	

FEATURES

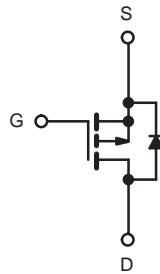
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC


RoHS
 COMPLIANT

SOT-363
 SC-70 (6-LEADS)



Top View



P-Channel MOSFET

APPLICATIONS

- Load Switch for Portable Devices
 - Cellular Phone
 - DSC
 - Portable Game Console
 - MP3
 - GPS

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	- 20	V	
Gate-Source Voltage	V_{GS}	± 12		
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	- 4 ^a	A	
	$T_C = 70$ °C	- 4		
	$T_A = 25$ °C	- 4 ^{a, b, c}		
	$T_A = 70$ °C	- 4 ^{a, b, c}		
Pulsed Drain Current ($t = 300$ μ s)	I_{DM}	- 25		
Continuous Source-Drain Diode Current	$T_C = 25$ °C	- 2.3		
	$T_A = 25$ °C	- 1.3 ^{b, c}		
Maximum Power Dissipation	$T_C = 25$ °C	2.8	W	
	$T_C = 70$ °C	1.8		
	$T_A = 25$ °C	1.6 ^{b, c}		
	$T_A = 70$ °C	1.0 ^{b, c}		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature)		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{b, d}	$t \leq 5$ s	R_{thJA}	60	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	34	45	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 5$ s.

d. Maximum under steady state conditions is 125 °C/W.

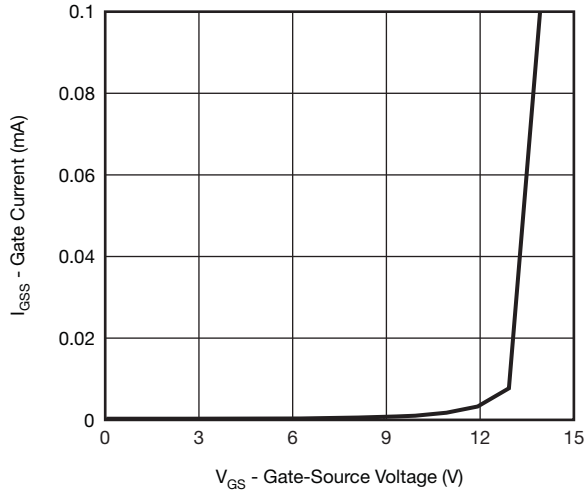
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-11		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		2.6			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.4		-1	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			± 8	μA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			± 1	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	-15			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$		0.034		Ω
		$V_{GS} = -2.5\text{ V}, I_D = -4.4\text{ A}$		0.045		
		$V_{GS} = -1.8\text{ V}, I_D = -1\text{ A}$		0.067		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -5\text{ A}$		16		S
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -8\text{ V}, I_D = -5\text{ A}$		22	33	nC
Gate-Source Charge		$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$		12.5	19	
Gate-Drain Charge	Q_{gs}		1.8			
	Q_{gd}		3.3			
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.08	0.43	0.86	k Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 1.4\text{ }\Omega$ $I_D \cong -4\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		150	225	ns
Rise Time	t_r			300	450	
Turn-Off Delay Time	$t_{d(off)}$			1620	2430	
Fall Time	t_f			560	840	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 1.4\text{ }\Omega$ $I_D \cong -4\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		50	100	
Rise Time	t_r			90	180	
Turn-Off Delay Time	$t_{d(off)}$			2500	3750	
Fall Time	t_f			600	900	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-2.3	A
Pulse Diode Forward Current	I_{SM}				-25	
Body Diode Voltage	V_{SD}	$I_S = -4\text{ A}, V_{GS} = 0\text{ V}$		-0.85	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -4\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		18	36	ns
Body Diode Reverse Recovery Charge	Q_{rr}			8	16	nC
Reverse Recovery Fall Time	t_a			18		ns
Reverse Recovery Rise Time	t_b			10		

Notes:

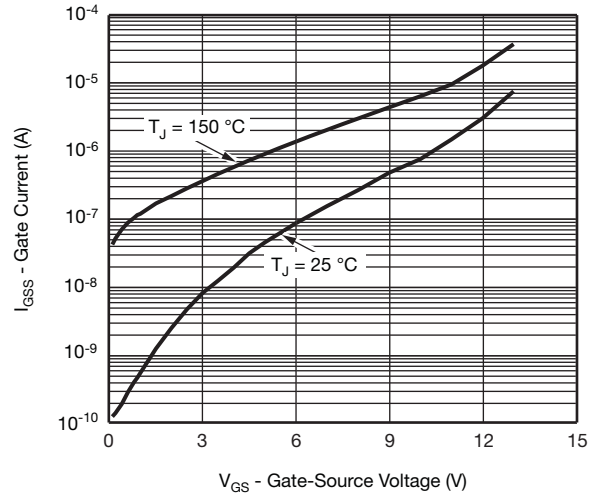
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

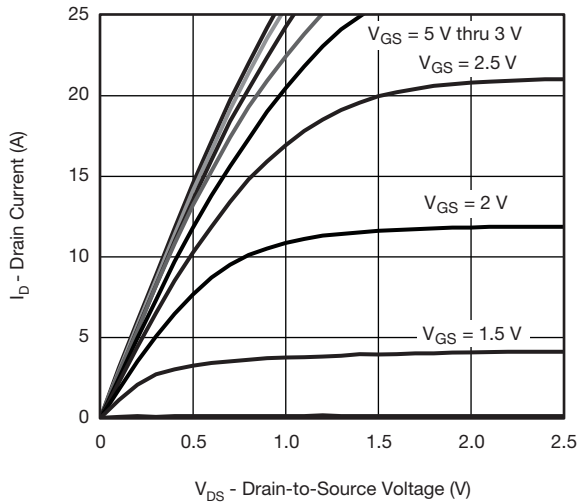
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



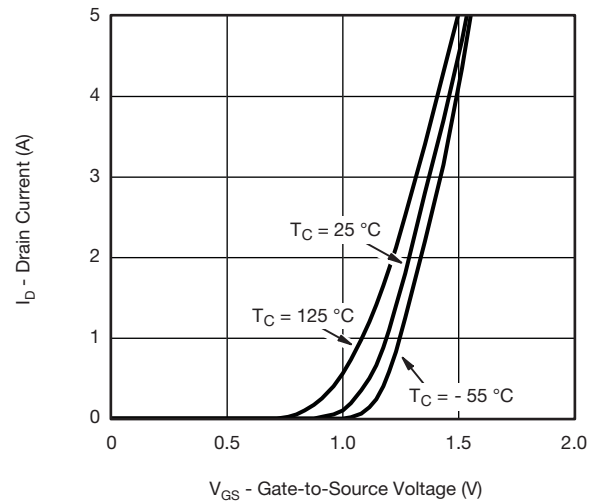
Gate Current vs. Gate-Source Voltage



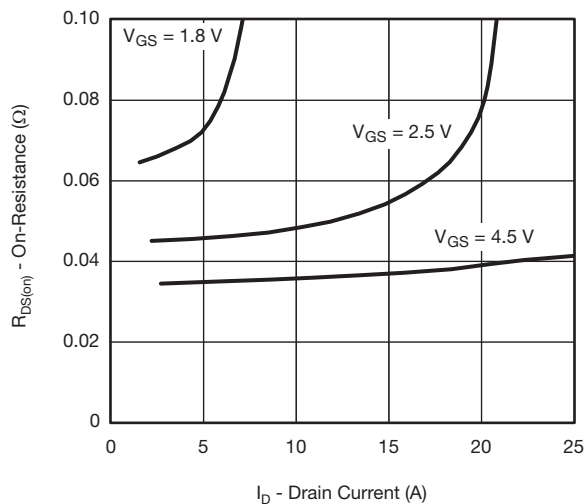
Gate Current vs. Gate-Source Voltage



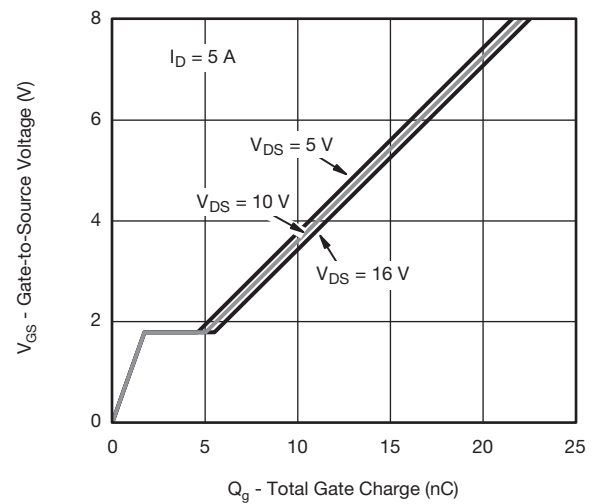
Output Characteristics



Transfer Characteristics

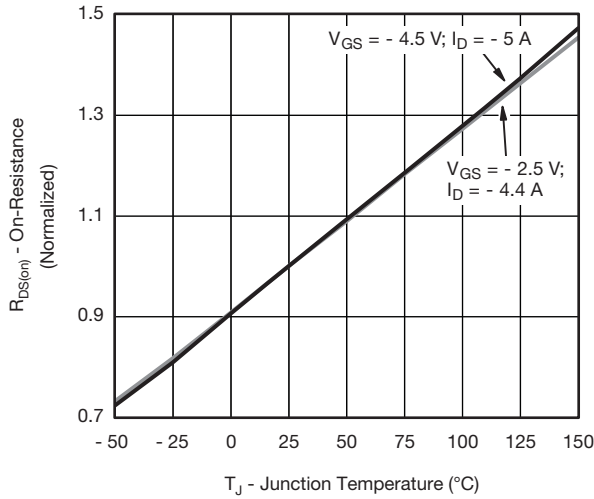


On-Resistance vs. Drain Current

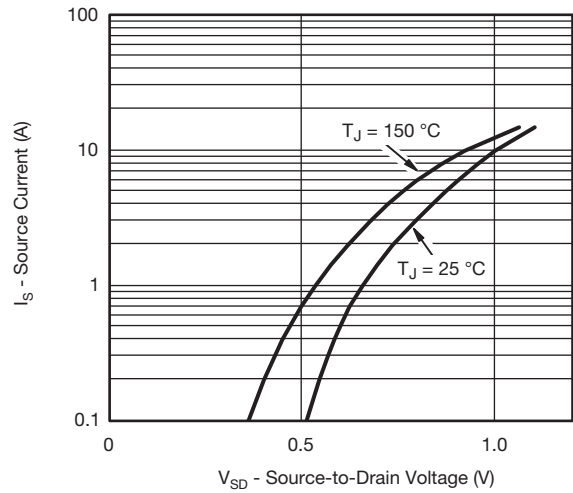


Gate Charge

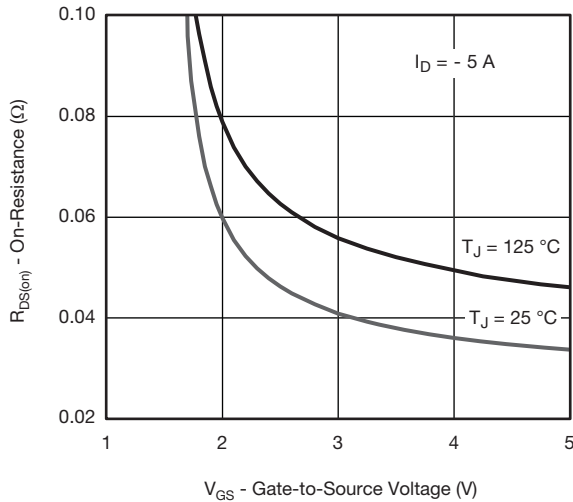
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



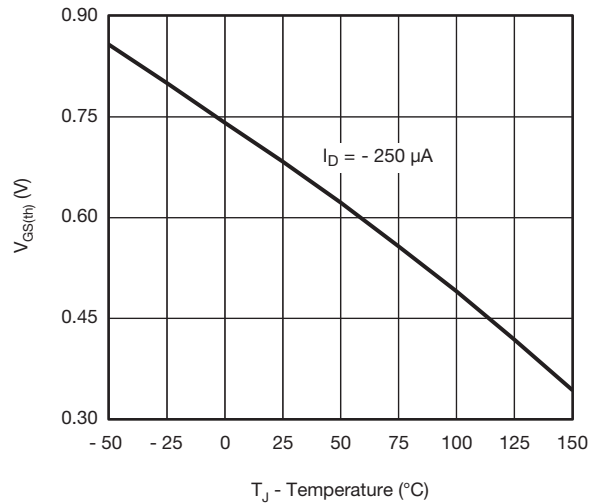
On-Resistance vs. Junction Temperature



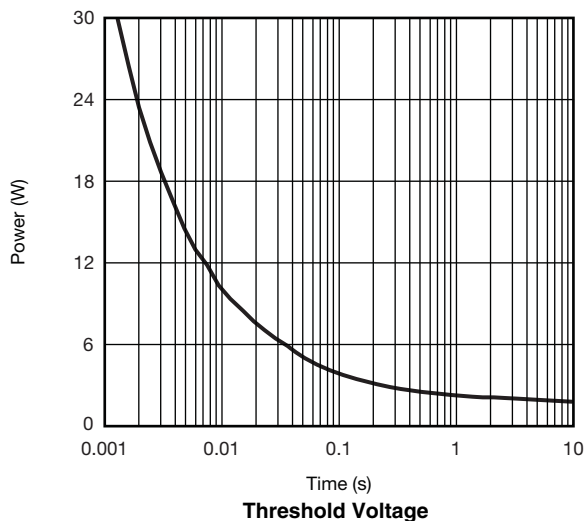
Source-Drain Diode Forward Voltage



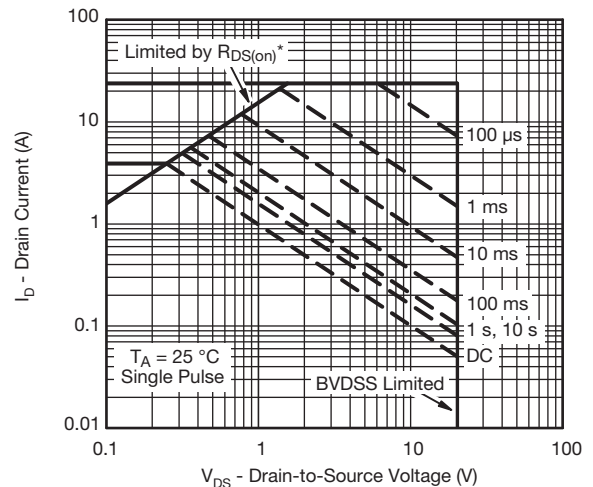
On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient

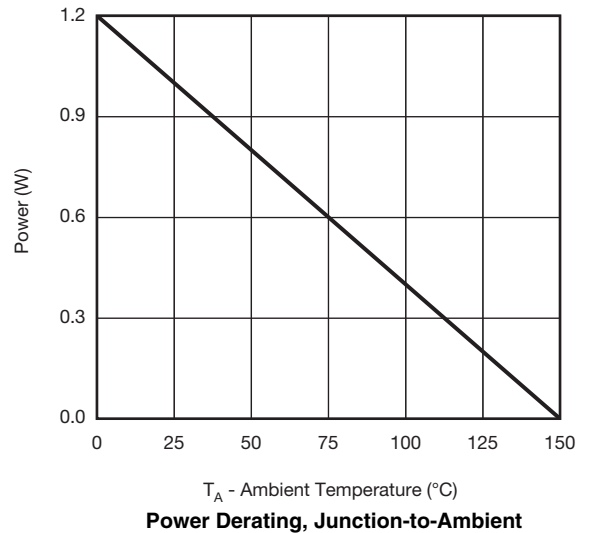
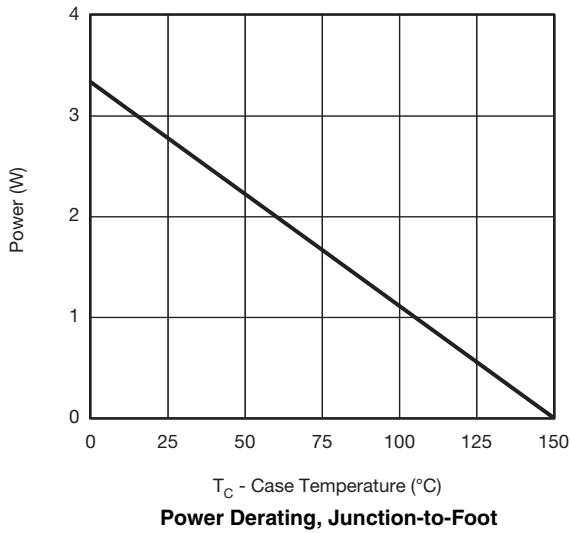
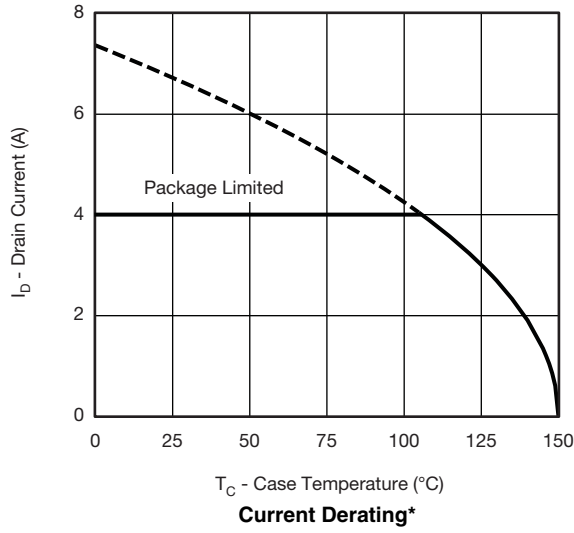


Threshold Voltage



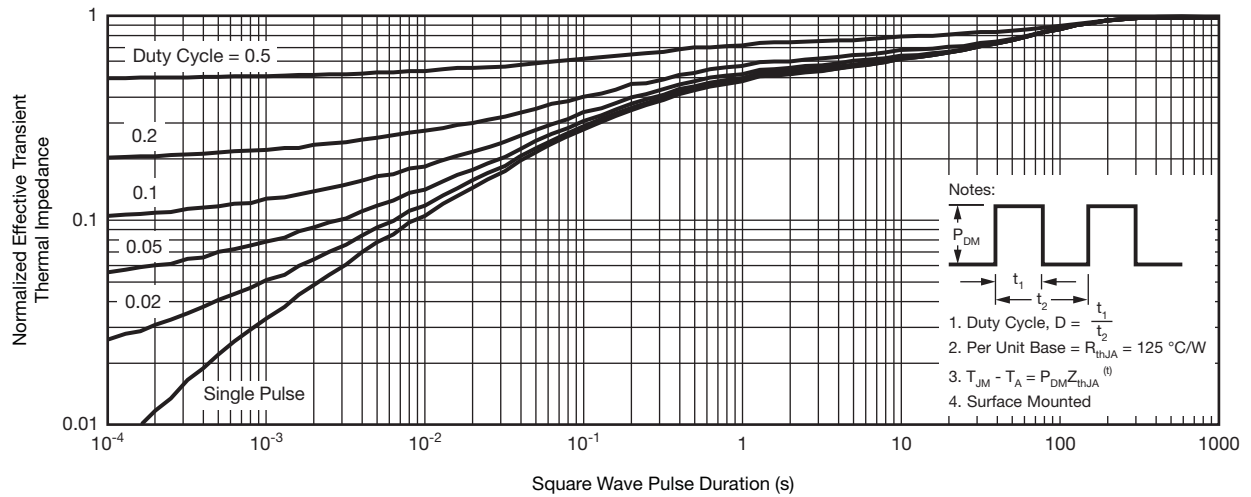
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

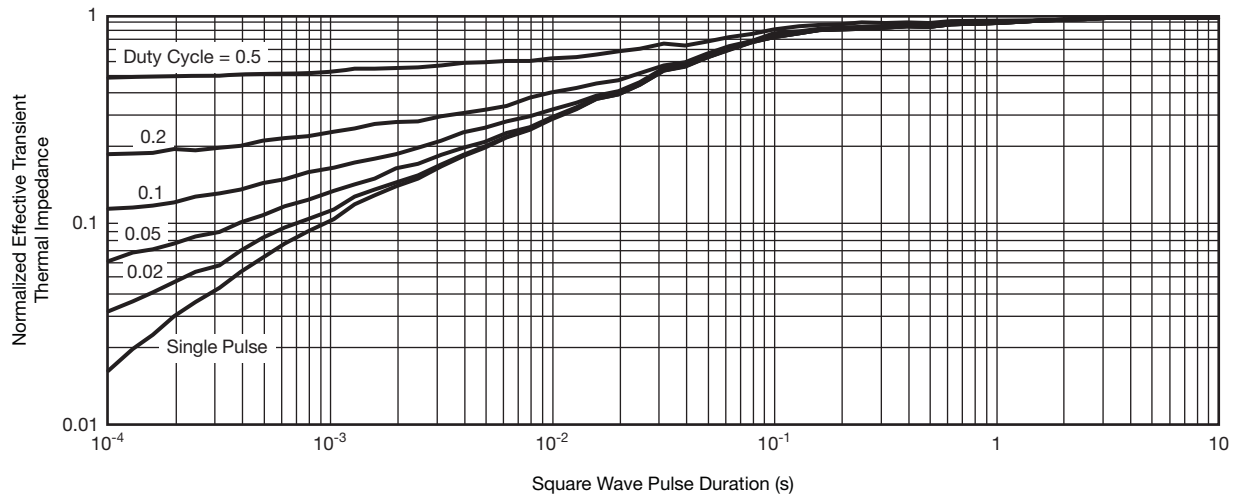


* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

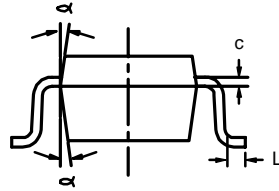
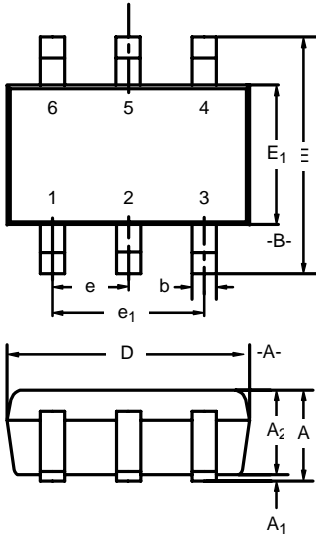


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

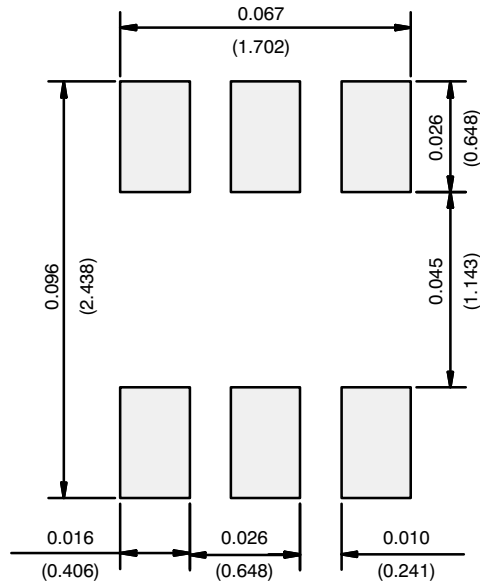
SC-70: 6-LEADS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	-	1.10	0.035	-	0.043
A ₁	-	-	0.10	-	-	0.004
A ₂	0.80	-	1.00	0.031	-	0.039
b	0.15	-	0.30	0.006	-	0.012
c	0.10	-	0.25	0.004	-	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		

ECN: S-03946—Rev. B, 09-Jul-01
DWG: 5550

RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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